TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# 2SC4325

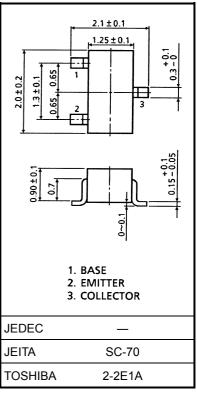
### VHF~UHF Band Low Noise Amplifier Applications

Unit: mm

- Low noise figure, high gain.
- NF = 1.8dB,  $|S_{21e}|^2 = 7.5$ dB (f = 2 GHz)

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	$V_{CBO}$	20	V	
Collector-emitter voltage	V <sub>CEO</sub>	10	V	
Emitter-base voltage	V <sub>EBO</sub>	1.5	V	
Base current	Ι <sub>Β</sub>	7	mA	
Collector current	I <sub>C</sub>	15	mA	
Collector power dissipation	P <sub>C</sub>	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	



#### Weight: 0.006 g (typ.)

### Microwave Characteristics (Ta = 25°C)

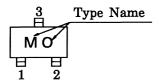
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit			
Transition frequency	f <sub>T</sub>	$V_{CE} = 6 \text{ V}, I_{C} = 7 \text{ mA}$	7	10	_	GHz			
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	1) $V_{CE} = 6 \text{ V}, I_{C} = 7 \text{ mA}, f = 1 \text{ GHz}$ — 13				dB			
mseriion gain	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 6 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	4.5	7.5	_	T ub			
Noise figure	NF (1)	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 3 mA, f = 1 GHz — 1.4		1.4	_	- dB			
Noise ligule	NF (2)	$V_{CE} = 6 \text{ V}, I_C = 3 \text{ mA}, f = 2 \text{ GHz}$	_	1.8	3.0	ub			

### **Electrical Characteristics (Ta = 25°C)**

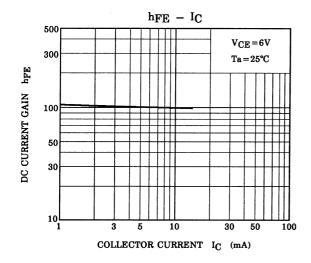
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μА
DC current gain	h <sub>FE</sub>	$V_{CE} = 6 \text{ V}, I_{C} = 7 \text{ mA}$	50	_	250	
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz (Note)	_	0.45	_	pF
Reverse transfer capacitance	C <sub>re</sub>	VCB = 10 V, 1E = 0, 1 = 1 WH 12 (Note)	_	0.35	0.8	pF

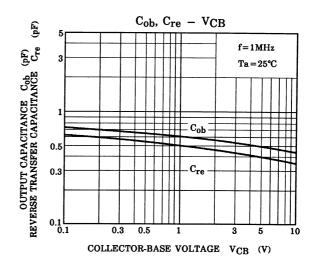
Note:  $C_{re}$  is measured by 3 terminal method with capacitance bridge.

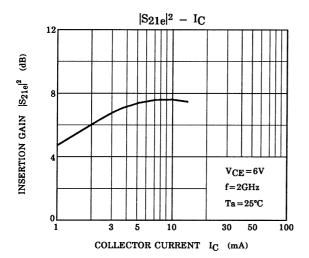
# Marking

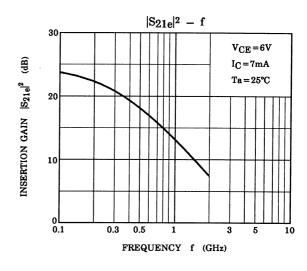


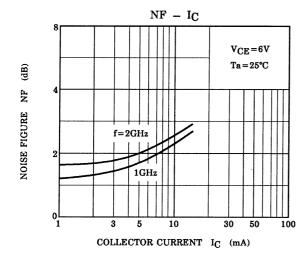
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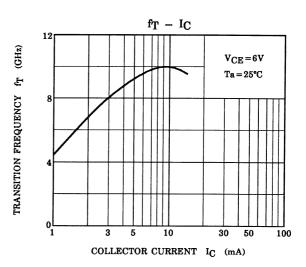




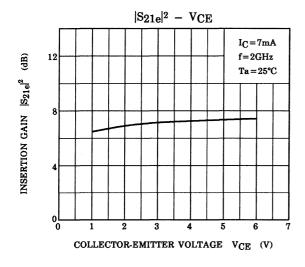


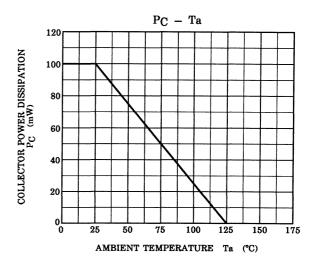






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## S-Parameter $Z_O = 50 \Omega$ , Ta = 25°C

### $V_{CE} = 6 V$ , $I_C = 3 mA$

Frequency	S	11	S	21	S1	12	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
200	0.778	-27.1	7.781	154.1	0.043	75.7	0.932	-18.5
400	0.641	-49.4	6.538	133.4	0.075	66.5	0.800	-31.9
600	0.500	-67.1	5.409	118.1	0.097	61.9	0.683	-40.4
800	0.394	-80.5	4.508	106.6	0.115	59.9	0.595	-45.8
1000	0.311	-93.1	3.809	97.9	0.132	59.4	0.536	-49.6
1200	0.238	-103.0	3.314	90.6	0.149	59.3	0.492	-52.7
1400	0.194	-114.5	2.909	84.0	0.165	59.3	0.465	-55.3
1600	0.146	-122.2	2.619	78.7	0.183	59.4	0.444	-57.9
1800	0.102	-135.3	2.409	73.5	0.199	59.4	0.428	-60.8
2000	0.074	-150.4	2.188	70.0	0.216	59.6	0.415	-64.2

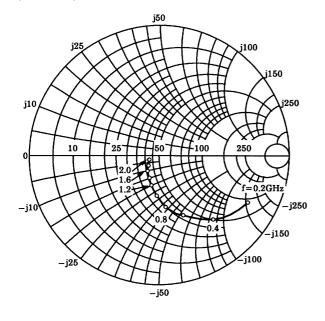
### $V_{CE} = 6 V$ , $I_C = 7 mA$

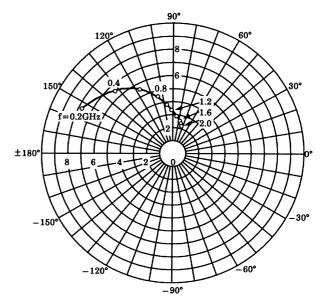
Frequency	S11		S21		S12		S22	
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
200	0.581	-39.7	12.614	141.9	0.037	73.0	0.842	-24.8
400	0.397	-64.8	9.040	119.2	0.061	67.7	0.652	-36.1
600	0.278	-82.1	6.744	105.5	0.081	67.3	0.541	-40.4
800	0.194	-94.9	5.328	96.2	0.101	67.7	0.477	-42.6
1000	0.137	-109.4	4.364	89.2	0.121	67.8	0.440	-44.3
1200	0.096	-123.2	3.733	83.2	0.141	67.8	0.417	-46.4
1400	0.062	-140.8	3.254	77.9	0.162	67.1	0.403	-48.5
1600	0.041	-169.5	2.899	73.4	0.183	66.6	0.394	-50.9
1800	0.030	137.0	2.634	68.9	0.203	65.6	0.389	-54.0
2000	0.038	99.1	2.377	66.1	0.222	65.1	0.382	-57.6

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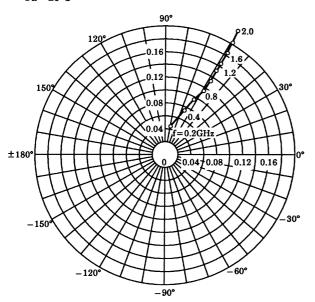
 $\begin{array}{l} S_{11e} \\ V_{CE} \!=\! 6V \\ I_{C} \!=\! 3mA \\ Ta \!=\! 25^{\circ}\! C \\ (UNIT:\Omega) \end{array}$ 



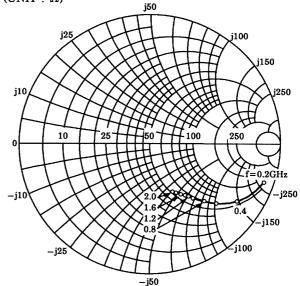




 $S_{12e}$   $V_{CE} = 6V$   $I_{C} = 3mA$   $T_{a} = 25^{\circ}C$ 

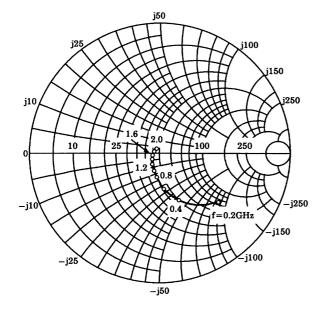


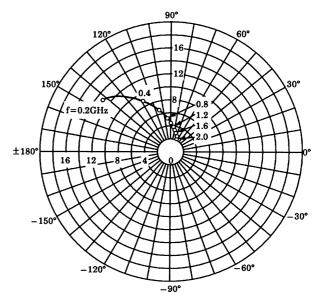
 $S_{22e}$   $V_{CE} = 6V$   $I_{C} = 3mA$   $T_{a} = 25^{\circ}C$   $(UNIT : \Omega)$ 



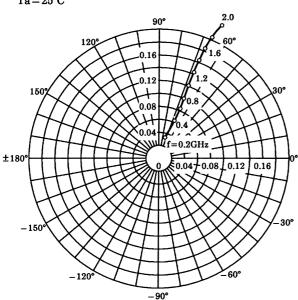
 $\begin{array}{l} S_{11e} \\ V_{CE} = 6V \\ I_{C} = 7mA \\ Ta = 25^{\circ}C \\ (UNIT:\Omega) \end{array}$ 



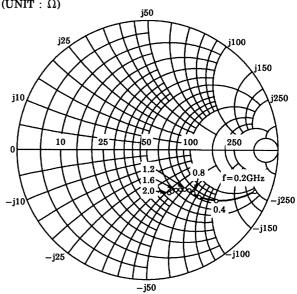




 $S_{12e}$   $V_{CE} = 6V$   $I_{C} = 7mA$   $T_{a} = 25^{\circ}C$ 



 $S_{22e}$   $V_{CE} = 6V$   $I_{C} = 7mA$   $T_{a} = 25^{\circ}C$   $(UNIT : \Omega)$ 



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